

# Hiroshi Yamaguchi

## List of Publications by Citations

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286  
papers

5,898  
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35  
h-index

67  
g-index

327  
ext. papers

6,630  
ext. citations

3.7  
avg, IF

5.75  
L-index

#	Paper	IF	Citations
286	Low-Temperature Growth of GaAs and AlAs-GaAs Quantum-Well Layers by Modified Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L868-L870	1.4	358
285	Migration-Enhanced Epitaxy of GaAs and AlGaAs. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, 169-179	1.4	331
284	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	301
283	Bit storage and bit flip operations in an electromechanical oscillator. <i>Nature Nanotechnology</i> , <b>2008</b> , 3, 275-9	28.7	208
282	Coherent phonon manipulation in coupled mechanical resonators. <i>Nature Physics</i> , <b>2013</b> , 9, 480-484	16.2	202
281	Motion detection of a micromechanical resonator embedded in a d.c. SQUID. <i>Nature Physics</i> , <b>2008</b> , 4, 785-788	16.2	146
280	Growth process of III-V compound semiconductors by migration-enhanced epitaxy. <i>Journal of Crystal Growth</i> , <b>1990</b> , 105, 326-338	1.6	141
279	Atomic-scale imaging of strain relaxation via misfit dislocations in highly mismatched semiconductor heteroepitaxy: InAs/GaAs(111)A. <i>Physical Review B</i> , <b>1997</b> , 55, 1337-1340	3.3	118
278	Interconnect-free parallel logic circuits in a single mechanical resonator. <i>Nature Communications</i> , <b>2011</b> , 2, 198	17.4	110
277	Inhibitions of three dimensional island formation in InAs films grown on GaAs (111)A surface by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 776-778	3.4	103
276	Imaging of Friedel oscillation patterns of two-dimensionally accumulated electrons at epitaxially grown InAs(111) A surfaces. <i>Physical Review Letters</i> , <b>2001</b> , 86, 3384-7	7.4	102
275	Phonon lasing in an electromechanical resonator. <i>Physical Review Letters</i> , <b>2013</b> , 110, 127202	7.4	101
274	Phonon-cavity electromechanics. <i>Nature Physics</i> , <b>2012</b> , 8, 387-392	16.2	99
273	Surface structure transitions on InAs and GaAs (001) surfaces. <i>Physical Review B</i> , <b>1995</b> , 51, 9836-9854	3.3	92
272	Phonon waveguides for electromechanical circuits. <i>Nature Nanotechnology</i> , <b>2014</b> , 9, 520-4	28.7	78
271	A Scanning Tunneling Microscopy-Reflection High Energy Electron Diffraction-Rate Equation Study of the Molecular Beam Epitaxial Growth of InAs on GaAs(001), (110) and (111)A Quantum Dots and Two-Dimensional Modes. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4111-4117	1.4	77
270	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 102106	3.4	77

269	Stacking domains of epitaxial few-layer graphene on SiC(0001). <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	74
268	A strict experimental test of macroscopic realism in a superconducting flux qubit. <i>Nature Communications</i> , <b>2016</b> , 7, 13253	17.4	73
267	Controllable coupling between flux qubit and nanomechanical resonator by magnetic field. <i>New Journal of Physics</i> , <b>2007</b> , 9, 35-35	2.9	64
266	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2009</b> , 2, 065502	2.4	59
265	Two-mode thermal-noise squeezing in an electromechanical resonator. <i>Physical Review Letters</i> , <b>2014</b> , 113, 167203	7.4	58
264	Two-dimensional growth of InSb thin films on GaAs(111)A substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 589-591	3.4	54
263	Replacement of group-III atoms on the growing surface during migration-enhanced epitaxy. <i>Journal of Applied Physics</i> , <b>1990</b> , 68, 1610-1615	2.5	54
262	Observation of Collective Coupling between an Engineered Ensemble of Macroscopic Artificial Atoms and a Superconducting Resonator. <i>Physical Review Letters</i> , <b>2016</b> , 117, 210503	7.4	50
261	An electromechanical Ising Hamiltonian. <i>Science Advances</i> , <b>2016</b> , 2, e1600236	14.3	48
260	Photoluminescence characteristics of AlGaAs-GaAs single quantum wells grown by migration-enhanced epitaxy at 300 °C substrate temperature. <i>Applied Physics Letters</i> , <b>1987</b> , 50, 1686-1687 <sup>4</sup>	3.4	47
259	A multimode electromechanical parametric resonator array. <i>Scientific Reports</i> , <b>2014</b> , 4, 4448	4.9	44
258	Vibration amplification, damping, and self-oscillations in micromechanical resonators induced by optomechanical coupling through carrier excitation. <i>Physical Review Letters</i> , <b>2011</b> , 106, 036801	7.4	42
257	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2008</b> , 6, 107-110	0.7	41
256	Gate-controlled electromechanical backaction induced by a quantum dot. <i>Nature Communications</i> , <b>2016</b> , 7, 11132	17.4	40
255	Step-Flow Growth on Vicinal GaAs Surfaces by Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L1456-L1459	1.4	40
254	Piezoelectrically pumped parametric amplification and Q enhancement in an electromechanical oscillator. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 173109	3.4	37
253	Local density of states in zero-dimensional semiconductor structures. <i>Physical Review Letters</i> , <b>2001</b> , 87, 196804	7.4	37
252	Local conductance measurements of double-layer graphene on SiC substrate. <i>Nanotechnology</i> , <b>2009</b> , 20, 445704	3.4	36

251	Proposed Robust Entanglement-Based Magnetic Field Sensor Beyond the Standard Quantum Limit. <i>Physical Review Letters</i> , <b>2015</b> , 115, 170801	7.4	35
250	Extremely long surface diffusion of Ga and critical nucleation on As-rich GaAs(001) surfaces caused by phase transitions. <i>Physical Review B</i> , <b>1997</b> , 56, 12080-12083	3.3	35
249	On-chip temporal focusing of elastic waves in a phononic crystal waveguide. <i>Nature Communications</i> , <b>2018</b> , 9, 1331	17.4	34
248	Single-Turn GaAs/InAs Nanotubes Fabricated Using the Supercritical CO <sub>2</sub> Drying Technique. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L791-L794	1.4	34
247	Unified Model for Structure Transition and Electrical Properties of InAs (001) Surfaces Studied by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, L1423-L1426	1.4	34
246	Influence of monomolecular steps on the first-order structure transition of an InAs(001) surface. <i>Physical Review Letters</i> , <b>1993</b> , 70, 1299-1302	7.4	33
245	Optical Tuning of Coupled Micromechanical Resonators. <i>Applied Physics Express</i> , <b>2009</b> , 2, 062202	2.4	32
244	Thickness-dependent electron accumulation in InAs thin films on GaAs(111)A: A scanning-tunneling-spectroscopy study. <i>Physical Review B</i> , <b>1998</b> , 58, R4219-R4222	3.3	32
243	Dispersive and dissipative coupling in a micromechanical resonator embedded with a nanomechanical resonator. <i>Nano Letters</i> , <b>2015</b> , 15, 2312-7	11.5	31
242	An electromechanical membrane resonator. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 063102	3.4	29
241	Improved resonance characteristics of GaAs beam resonators by epitaxially induced strain. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251913	3.4	29
240	GaAs-based micro/nanomechanical resonators. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 103003	1.8	28
239	Entangled-state generation and Bell inequality violations in nanomechanical resonators. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	28
238	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 8305-8310	1.4	28
237	Tunable backaction of a DC SQUID on an integrated micromechanical resonator. <i>Physical Review Letters</i> , <b>2010</b> , 105, 207203	7.4	27
236	Cooling of a micro-mechanical resonator by the back-action of Lorentz force. <i>New Journal of Physics</i> , <b>2008</b> , 10, 043015	2.9	27
235	A phonon transistor in an electromechanical resonator array. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 213102	3.4	26
234	Two-Dimensional Patterning of Flexible Designs with High Half-Pitch Resolution by Using Block Copolymer Lithography. <i>Advanced Materials</i> , <b>2008</b> , 20, 1684-1689	2.4	26

233	Excellent electric properties of free-standing InAs membranes. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2372-2374	3.4	26
232	Direct comparison of GaAs surface morphology between migration enhanced epitaxy and molecular beam epitaxy using in situ scanning electron microscopy. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 63-65	3.4	25
231	High-sensitivity charge detection using antisymmetric vibration in coupled micromechanical oscillators. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 014103	3.4	24
230	Spin dynamics of two-dimensional electrons in a quantum Hall system probed by time-resolved Kerr rotation spectroscopy. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	24
229	From ferro- to antiferromagnetism via exchange-striction of MnAs/GaAs(001). <i>Europhysics Letters</i> , <b>2005</b> , 72, 479-485	1.6	23
228	Optically detected magnetic resonance of high-density ensemble of NV centers in diamond. <i>Journal of Physics Condensed Matter</i> , <b>2016</b> , 28, 275302	1.8	23
227	Microelectromechanical displacement sensing using InAs/AlGaSb heterostructures. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 394-396	3.4	22
226	First-order surface-structure transition on the (001) InAs surface studied with improved high-energy electron reflectivity measurements. <i>Physical Review B</i> , <b>1992</b> , 45, 1511-1513	3.3	22
225	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. <i>Applied Physics Express</i> , <b>2013</b> , 6, 055101	2.4	21
224	Multi-mode parametric coupling in an electromechanical resonator. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 153105	3.4	21
223	Parametrically pumped ultrahigh Q electromechanical resonator. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 253109	3.4	21
222	Imaging of layer by layer growth processes during molecular beam epitaxy of GaAs on (111)A substrates by scanning electron microscopy. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 3079-3081	3.4	21
221	Hopf and period-doubling bifurcations in an electromechanical resonator. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 073101	3.4	21
220	Limit cycles and bifurcations in a nonlinear MEMS resonator with a 1:3 internal resonance. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 103103	3.4	20
219	Improving the coherence time of a quantum system via a coupling to a short-lived system. <i>Physical Review Letters</i> , <b>2015</b> , 114, 120501	7.4	20
218	Cavity-less on-chip optomechanics using excitonic transitions in semiconductor heterostructures. <i>Nature Communications</i> , <b>2015</b> , 6, 8478	17.4	20
217	Quantum point contact displacement transducer for a mechanical resonator at sub-Kelvin temperatures. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 192105	3.4	20
216	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. <i>Nanotechnology</i> , <b>2008</b> , 19, 495701	3.4	20

215	Step motion and As desorption on InAs(001) surfaces observed by scanning tunneling microscopy. <i>Physical Review B</i> , <b>1993</b> , 48, 2807-2810	3.3	20
214	Scanning tunneling microscopy observation of monolayer steps on GaAs(001) vicinal surfaces grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 678-680	3.4	20
213	Scanning tunneling microscopy studies of strain relaxation and misfit dislocations in InAs layers grown on GaAs(110) and GaAs(111)A. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1997</b> , 15, 915-918	2.9	19
212	Wide-band idler generation in a GaAs electromechanical resonator. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	18
211	Growth of very-high-mobility AlGaSb/InAs high-electron-mobility transistor structure on si substrate for high speed electronic applications. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 023509	3.4	18
210	Improving the lifetime of the nitrogen-vacancy-center ensemble coupled with a superconducting flux qubit by applying magnetic fields. <i>Physical Review A</i> , <b>2015</b> , 91,	2.6	17
209	Parametric mode mixing in asymmetric doubly clamped beam resonators. <i>New Journal of Physics</i> , <b>2013</b> , 15, 015023	2.9	17
208	Contact Conductance Measurement of Locally Suspended Graphene on SiC. <i>Applied Physics Express</i> , <b>2010</b> , 3, 045101	2.4	17
207	Electron-spin manipulation and resonator readout in a double-quantum-dot nanoelectromechanical system. <i>Physical Review Letters</i> , <b>2008</b> , 100, 136802	7.4	17
206	Influence of surface reconstruction on the As desorption process from a (001) GaAs surface evaluated by improved high-energy electron-reflectivity measurements. <i>Physical Review B</i> , <b>1991</b> , 44, 5897-5900	3.3	17
205	Influence of an As-Free Atmosphere in Migration-Enhanced Epitaxy on Step-Flow Growth. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 802-808	1.4	17
204	Growth of GaAs/ErAs/GaAs structures by migration-enhanced epitaxy. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 2341-2343	3.4	17
203	Self-sustained oscillations of a torsional SQUID resonator induced by Lorentz-force back-action. <i>Nature Communications</i> , <b>2013</b> , 4, 1803	17.4	16
202	A $\delta$ -Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 1617-1625	2.9	16
201	Force/displacement detection using quantum transport in InAs/AlGaSb two-dimensional heterostructures. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 052106	3.4	16
200	Flattening Transition on GaAs (411)A Surfaces Observed by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1995</b> , 34, L1490-L1493	1.4	16
199	Surface-defect formation on heavily doped InAs and GaAs layers studied by scanning tunneling microscopy. <i>Physical Review B</i> , <b>1996</b> , 53, 4565-4569	3.3	16
198	Surface Migration of Ga and Al Atoms on (100) GaAs and AlAs during Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, 1307-1311	1.4	16

197	A strongly coupled Etype micromechanical system. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 153105	3.4	16
196	Phonon propagation dynamics in band-engineered one-dimensional phononic crystal waveguides. <i>New Journal of Physics</i> , <b>2015</b> , 17, 113032	2.9	15
195	Rapid switching in high-Q mechanical resonators. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 083114	3.4	15
194	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	15
193	Improvement in the Electrical Properties of GaAs/InAs/GaAs Structures through the Use of (111)A Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 1599-1602	1.4	15
192	Drastic Improvement in Surface Flatness Properties by Using GaAs (111)A Substrates in Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 635-644	1.4	15
191	Dependence of ErAs Clustering and Er Segregation in ErAs/GaAs Heterostructures on Growth Temperature. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L1784-L1787	1.4	15
190	As desorption from GaAs and AlAs surfaces studied by improved high-energy electron reflectivity measurements. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 1753-1759	2.5	15
189	Electron paramagnetic resonance spectroscopy using a single artificial atom. <i>Communications Physics</i> , <b>2019</b> , 2,	5.4	14
188	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. <i>Sensors and Actuators A: Physical</i> , <b>2013</b> , 197, 122-125	3.9	14
187	Coherent Control of Micro/Nanomechanical Oscillation Using Parametric Mode Mixing. <i>Applied Physics Express</i> , <b>2012</b> , 5, 014001	2.4	14
186	First principles and macroscopic theories of semiconductor epitaxial growth. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 206-211	1.6	14
185	Impact-parameter dependent stopping powers for axially channeled and semichanneled MeV He ions in GaAs:Er. <i>Physical Review B</i> , <b>1994</b> , 49, 14387-14396	3.3	14
184	Electron paramagnetic resonance spectroscopy using a direct current-SQUID magnetometer directly coupled to an electron spin ensemble. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 052601	3.4	14
183	Enhanced force sensitivity and noise squeezing in an electromechanical resonator coupled to a nanotransistor. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 253105	3.4	13
182	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and 295K. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	13
181	Infrared detection with silicon nano-field-effect transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 223108	3.4	13
180	Step Motion and Structure Transition on InAs and GaAs (001) Surfaces Observed by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, 716-720	1.4	13

179	Broadband reconfigurable logic gates in phonon waveguides. <i>Scientific Reports</i> , <b>2017</b> , 7, 12745	4.9	12
178	Electrostatically Induced Phononic Crystal. <i>Physical Review Applied</i> , <b>2019</b> , 11,	4.3	12
177	Mechanical random access memory in a phonon circuit. <i>Applied Physics Express</i> , <b>2014</b> , 7, 125201	2.4	12
176	A symmetry-breaking electromechanical detector. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 213103	3.4	12
175	Device linearity comparison of uniformly doped and $\delta$ -doped In <sub>0.52</sub> Al <sub>0.48</sub> /As <sub>0.6</sub> /Ga <sub>0.4</sub> /As metamorphic HEMTs. <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 535-537	4.4	12
174	Resist-Pattern Guided Self-assembly of Symmetric Diblock Copolymer. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , <b>2006</b> , 19, 385-388	0.7	12
173	Magnetoelastic coupling of MnAs <sub>2</sub> /GaAs(001) close to the phase transition. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	12
172	Fabrication of conductive single-crystal semiconductor nanoscale electromechanical structures. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4428-4430	3.4	12
171	Structural analysis of erbium sheet-doped GaAs grown by molecular-beam epitaxy, with ion channeling followed by Monte Carlo simulation. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 3095-3103	2.5	12
170	Dynamic Control of the Coupling between Dark and Bright Excitons with Vibrational Strain. <i>Physical Review Letters</i> , <b>2018</b> , 120, 267401	7.4	12
169	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CH01	1.4	11
168	Magneto-optical spectroscopy of excitons and trions in charge-tunable quantum dots. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	11
167	Room temperature piezoelectric displacement detection via a silicon field effect transistor. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 233102	3.4	11
166	Quantum interference effects in the magnetopiezoresistance of InAs/AlGaSb quasi-one-dimensional electron systems. <i>Physical Review Letters</i> , <b>2004</b> , 93, 036603	7.4	11
165	Microscopic investigation of the surface phase transition on GaAs(001) surfaces. <i>Surface Science</i> , <b>1999</b> , 433-435, 382-386	1.8	11
164	Superfield perturbation theory in harmonic superspace. <i>Physical Review D</i> , <b>1985</b> , 32, 1954-1967	4.9	11
163	An opto-electro-mechanical system based on evanescently-coupled optical microbottle and electromechanical resonator. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 201103	3.4	11
162	Discrete-time quadrature feedback cooling of a radio-frequency mechanical resonator. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 013113	3.4	10



161	Thermoelastic damping in GaAs micromechanical resonators. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 2920-2922		10
160	Nanogap electrodes on Si cantilever for local conductance measurement. <i>Journal of Physics: Conference Series</i> , <b>2007</b> , 61, 856-860	0.3	10
159	Electronic properties of monolayer steps on (2 x 4)/c(2 x 8) reconstructed GaAs(001) surfaces. <i>Physical Review B</i> , <b>1996</b> , 54, 4428-4431	3.3	10
158	Anomalous Distribution of In Atoms in GaAs during Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L2010-L2012	1.4	10
157	Dynamical coupling between a nuclear spin ensemble and electromechanical phonons. <i>Nature Communications</i> , <b>2018</b> , 9, 2993	17.4	10
156	Mechanical Kerr Nonlinearity of Wave Propagation in an On-Chip Nanoelectromechanical Waveguide. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	9
155	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2010</b> , 3, 115103	2.4	9
154	Spatial and temporal modulation of exciton photoluminescence properties in GaAs/AlAs dynamic quantum dots formed by surface acoustic waves. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	9
153	Three-dimensional alignment with 10nm order accuracy in electron-beam lithography on rotated sample for three-dimensional nanofabrication. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 2529-2533	9	
152	Flexible Nanofabrication in Three-Dimensional Electron-Beam Lithography Enhanced by Suppression of Proximity Effect. <i>Applied Physics Express</i> , <b>2008</b> , 1, 097001	2.4	9
151	First-principles calculation for misfit dislocations in InAs/GaAs(110) heteroepitaxy. <i>Surface Science</i> , <b>1999</b> , 433-435, 900-903	1.8	9
150	N = 2 harmonic superspace with central charges and its application to self-interacting massive hypermultiplets. <i>Annals of Physics</i> , <b>1986</b> , 172, 26-39	2.5	9
149	Virtual Exceptional Points in an Electromechanical System. <i>Physical Review Applied</i> , <b>2019</b> , 11,	4.3	8
148	Demonstration of Multiple Internal Resonances in a Microelectromechanical Self-Sustained Oscillator. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	8
147	Ferromagnetic-induced component in piezoresistance of GaMnAs. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	8
146	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 064304	2.5	8
145	Superconductivity in Tungsten-Carbide Nanowires Deposited from the Mixtures of W(CO) <sub>6</sub> and C <sub>14</sub> H <sub>10</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 075001	1.4	8
144	Ultrahigh-Q Micromechanical Resonators by Using Epitaxially Induced Tensile Strain in GaNAs. <i>Applied Physics Express</i> , <b>2013</b> , 6, 111201	2.4	8

143	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 070115	1.4	8
142	Carbon Multiprobe on a Si Cantilever for Pseudo-Metal Oxide Semiconductor Field-Effect-Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 2009-2013	1.4	8
141	Photoluminescence Dynamics of GaAs/AlAs Quantum Wells Modulated by Surface Acoustic Waves. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L758-L760	1.4	8
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